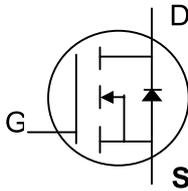




N-channel Enhancement-mode Power MOSFET

- Simple Drive Requirement**
- Low Gate Charge**
- Fast Switching Performance**
- RoHS-compliant, halogen-free**

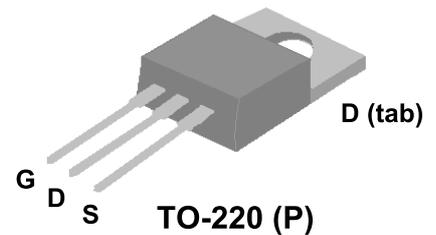


BV_{DSS}	30V
$R_{DS(ON)}$	17mΩ
I_D	40A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.

The AP40N03GP-HF-3 is in the TO-220 through-hole package which is used in commercial applications where a low PCB footprint or an attached heatsink is required. This device is well suited for low voltage applications such as DC/DC converters and high current DC switches.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D at $T_C=25^\circ C$	Continuous Drain Current	40	A
I_D at $T_C=100^\circ C$	Continuous Drain Current	30	A
I_{DM}	Pulsed Drain Current ¹	169	A
P_D at $T_C=25^\circ C$	Total Power Dissipation	50	W
P_D at $T_A=25^\circ C$	Total Power Dissipation	2	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	2.5	°C/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient	62	°C/W

Ordering Information

AP40N03GP-HF-3TB : in RoHS-compliant halogen-free TO-220, shipped in tubes (50pcs/tube)